

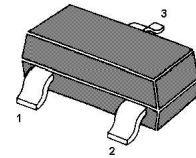
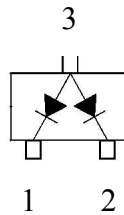
# Olitech Electronics Co.,Ltd

Email: [info@olitech-elec.com](mailto:info@olitech-elec.com) Website: [www.olitech-elec.com](http://www.olitech-elec.com)

## BAS35 Silicon Epitaxial Planar Switching Diode

### Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance



### Applications

- Ultra high speed switching application

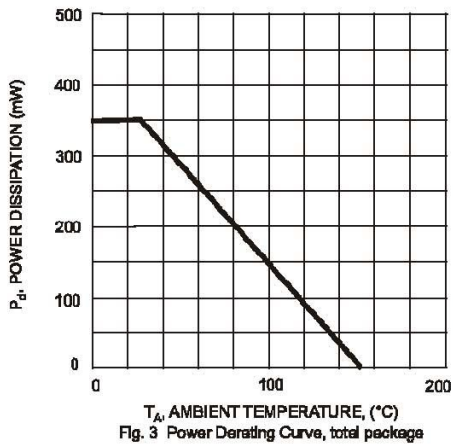
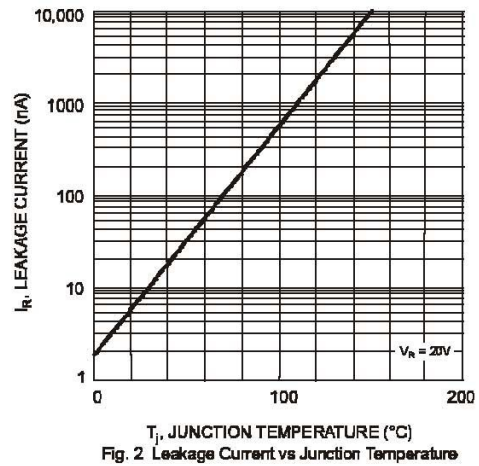
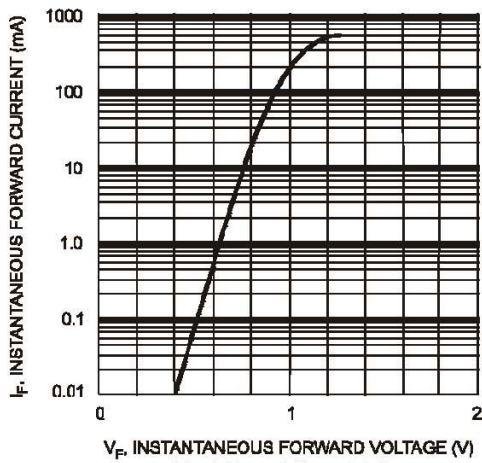
Marking Code: **A3**  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$	85	V
Continuous Reverse Voltage	$V_R$	75	V
Forward Current (DC) Single Diode Loaded Double Diode Loaded	$I_F$	215 125	mA
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-repetitive Peak Forward Surge Current at $t = 1$ s at $t = 1$ ms at $t = 1$ $\mu$ s	$I_{FSM}$	0.5 1 4	A
Power Dissipation	$P_{tot}$	350	mW
Operating Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

### Characteristics at Ta = 25°C

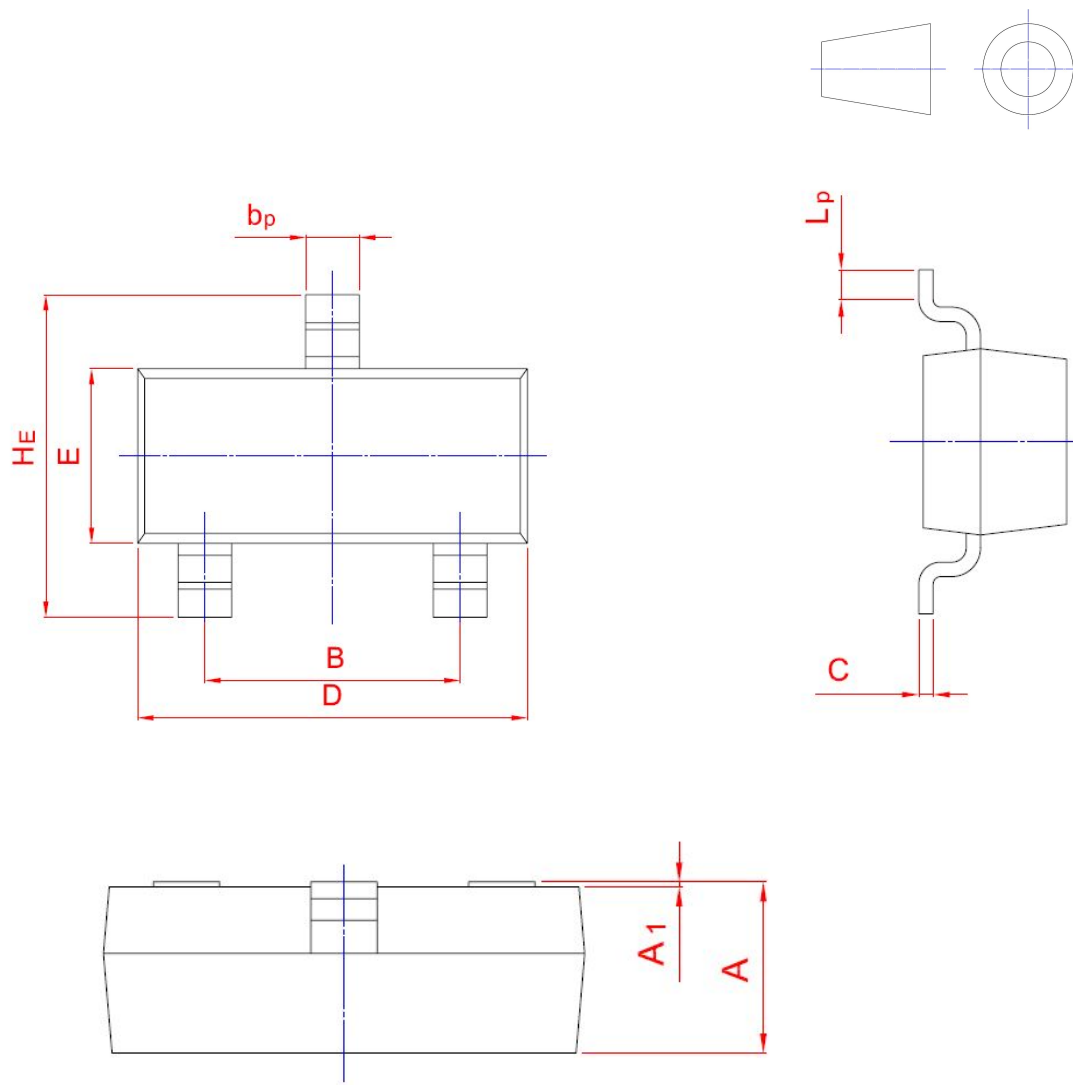
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	$V_F$	715	mV
	$V_F$	855	mV
	$V_F$	1	V
	$V_F$	1.25	V
Reverse Current at $V_R = 25 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 25 \text{ V}, T_J = 150^\circ\text{C}$ at $V_R = 75 \text{ V}, T_J = 150^\circ\text{C}$	$I_R$	30	nA
	$I_R$	1	$\mu\text{A}$
	$I_R$	30	$\mu\text{A}$
	$I_R$	50	$\mu\text{A}$
Diode Capacitance at $V_R = 0, f = 1 \text{ MHz}$	$C_d$	2	pF
Reverse Recovery Time at $I_F = I_R = 10 \text{ mA}, R_L = 100\Omega$	$t_{rr}$	4	ns



# Package Outline

Plastic surface mounted package, 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20